

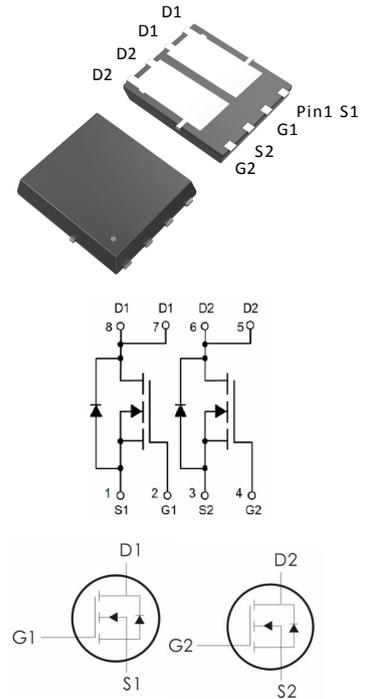
Description:

This Dual N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=40A, R_{DS(ON)} < 14m\Omega @ V_{GS}=10V$ (Typ: $11m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density SGT technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
NE014DTG-B	E014DT-B	DFN5*6-8D	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹	40	A
	Continuous Drain Current- $T_C=100^\circ C$ ¹	28	
I_{DM}	Pulsed Drain Current ²	160	
P_D	Power Dissipation	33	W
E_{AS}	Single pulse avalanche energy ³	49	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.8	$^\circ C/W$

Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=60V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics <small>(Note3)</small>						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1	1.5	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ⁴	$V_{GS}=10V, I_D=20A$	---	11	14	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	13.5	17.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	869	---	pF
C_{oss}	Output Capacitance		---	388	--	
C_{rss}	Reverse Transfer Capacitance		---	31	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V, I_D=10A,$ $R_G=4.7\ \Omega, V_{GS}=10V$	---	9	---	ns
t_r	Rise Time		---	19.4	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	33	---	ns
t_f	Fall Time		---	8.9	---	ns
Q_g	Total Gate Charge		$V_{GS}=10V, V_{DS}=30V,$ $I_D=10A$	---	16	---
Q_{gs}	Gate-Source Charge	---		5.3	---	nC
Q_{gd}	Gate-Drain "Miller" Charge	---		6.4	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=10A$	---	---	1.2	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	40	A
I_{SM}	Pulsed Drain Current		---	---	160	A

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C, V_{DD}=30V, V_G=10V, L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_C=25^{\circ}C$ unless otherwise noted)

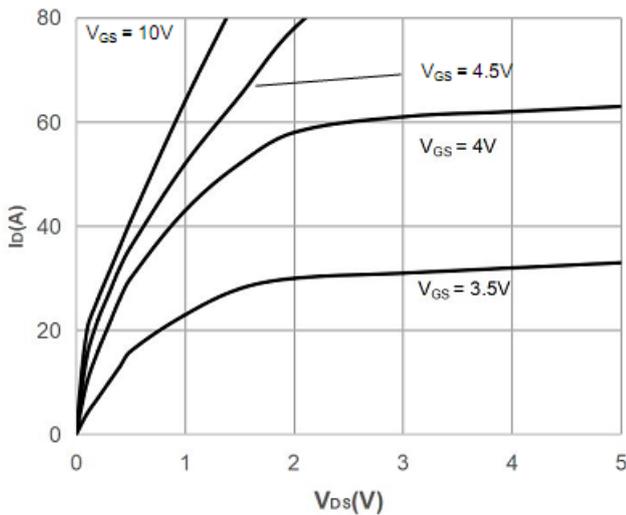


Figure 1: Output Characteristics

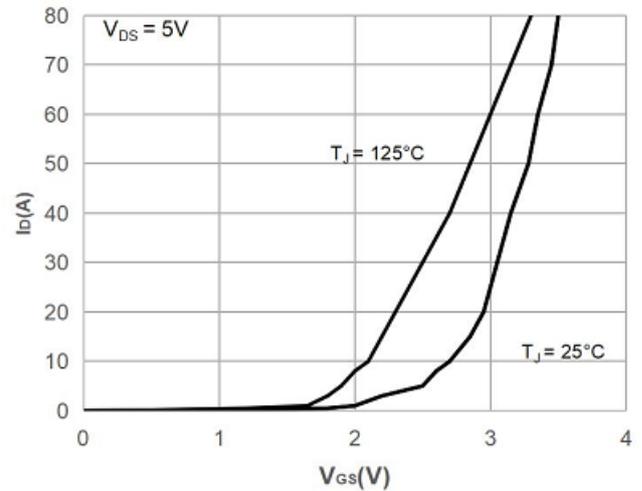


Figure 2: Typical Transfer Characteristics

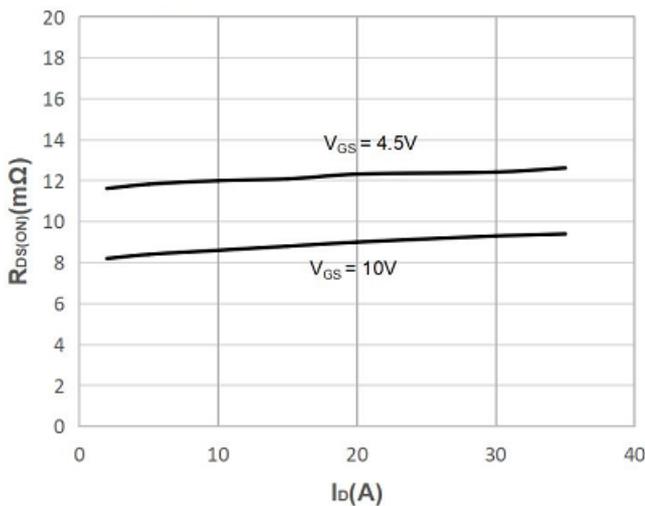


Figure 3: On-resistance vs. Drain Current

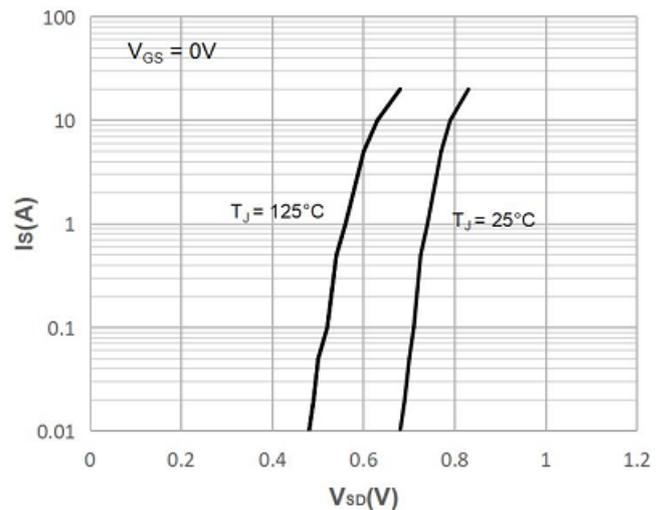


Figure 4: Body Diode Characteristics

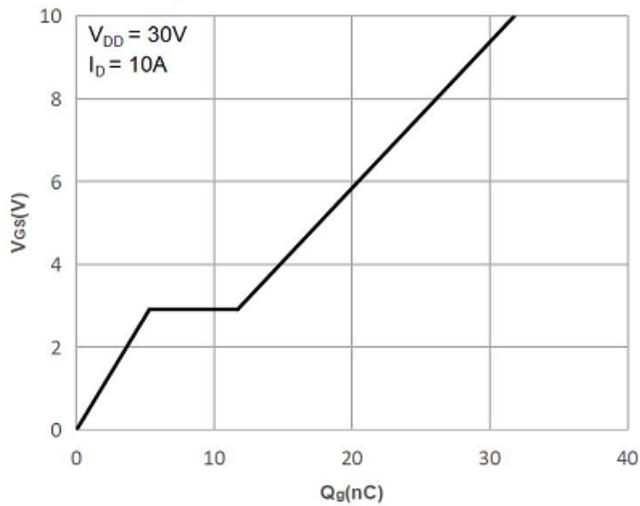


Figure 5: Gate Charge Characteristics

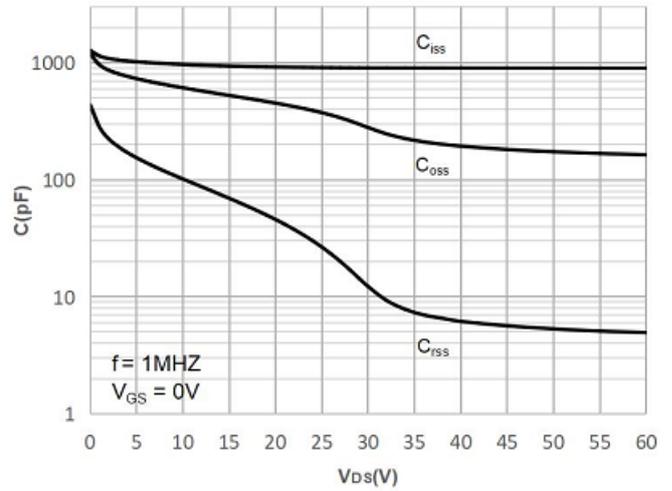


Figure 6: Capacitance Characteristics

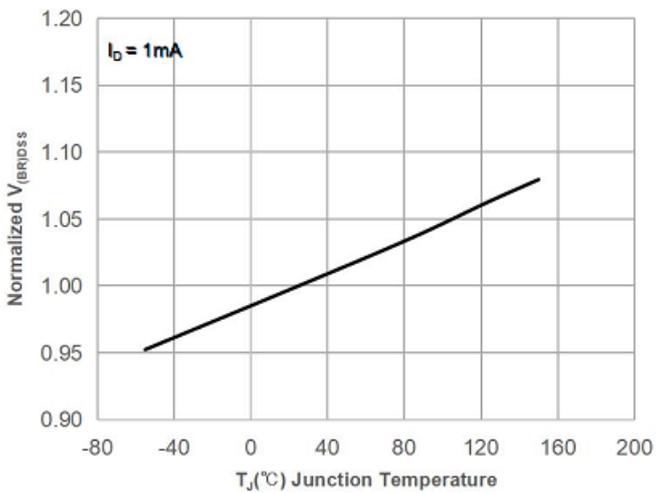


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

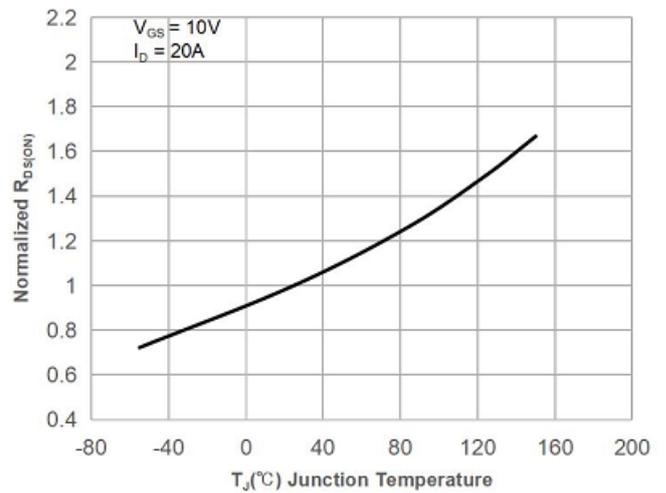


Figure 8: Normalized on Resistance vs. Junction Temperature

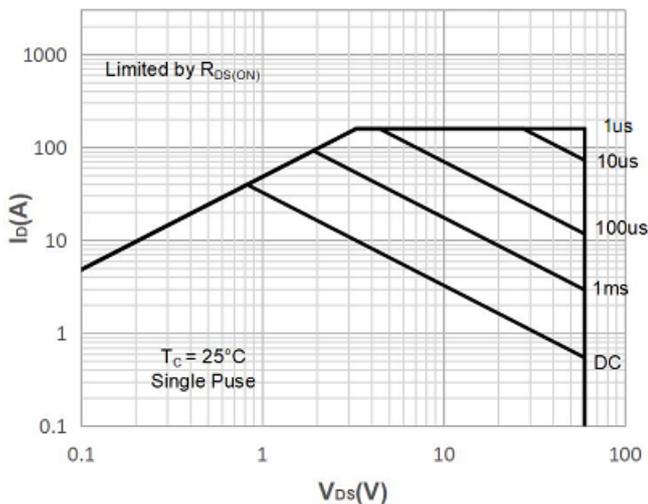


Figure 9: Maximum Safe Operating Area

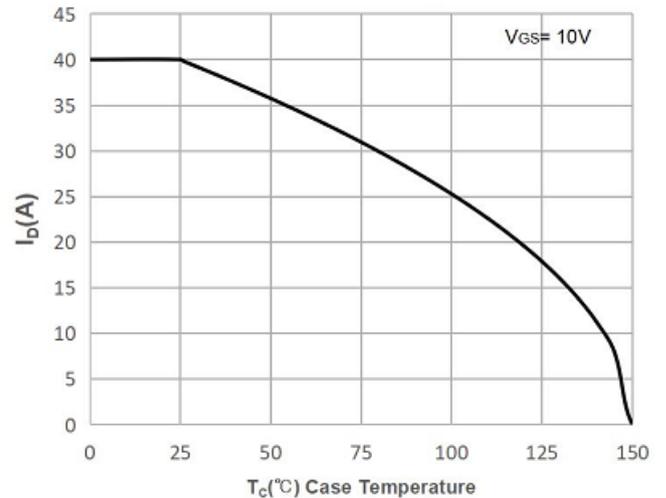


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

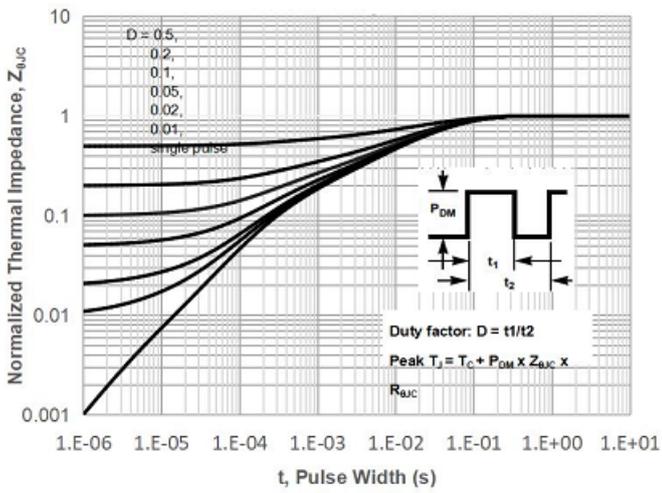


Figure 11: Normalized Maximum Transient Thermal Impedance

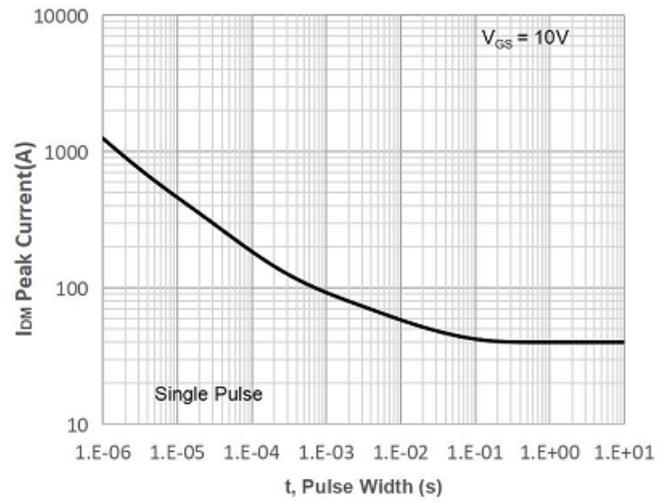
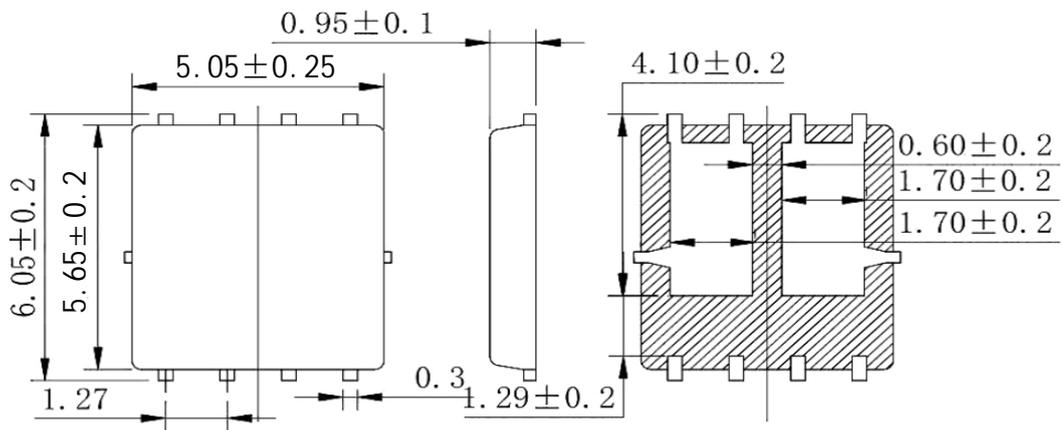
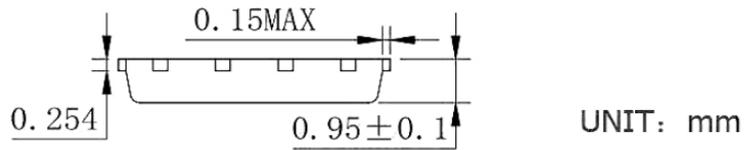


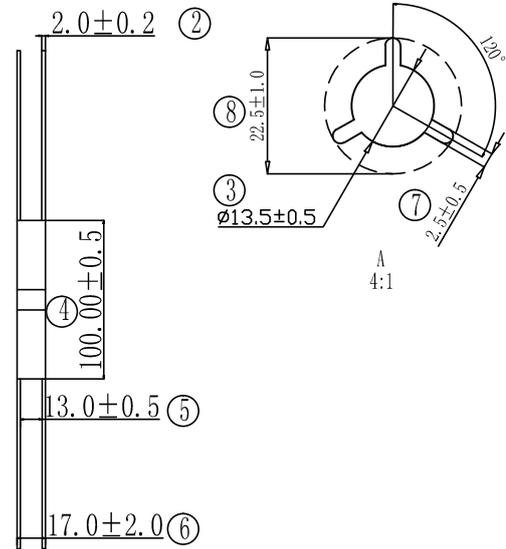
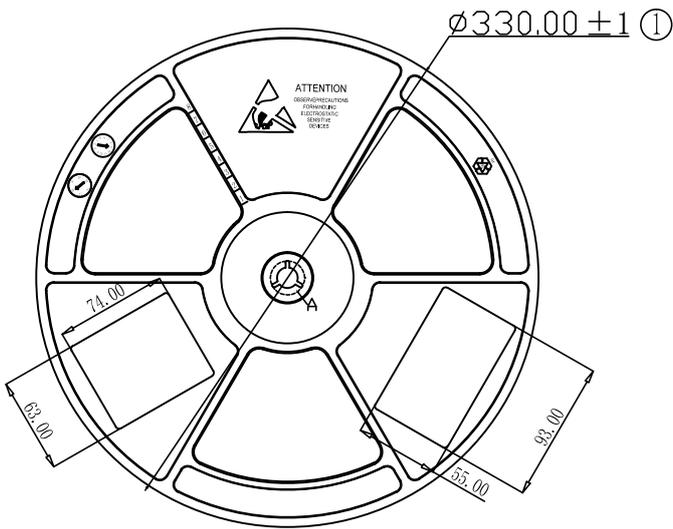
Figure 12: Peak Current Capacity

DFN5X6-8D Package Information:

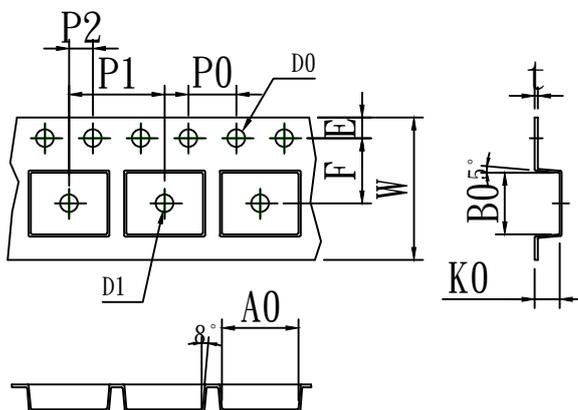


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15 ± 0.10	5.40 ± 0.10	1.30 ± 0.10	1.55 ± 0.10	1.55 ± 0.10	4.00 ± 0.10	8.00 ± 0.10	40.00 ± 0.10
Symbol	W	E	F	P2	t			
Spec	12.00 ± 0.10	1.75 ± 0.10	5.50 ± 0.10	2.00 ± 0.10	0.20 ± 0.05			



Pulling direction 

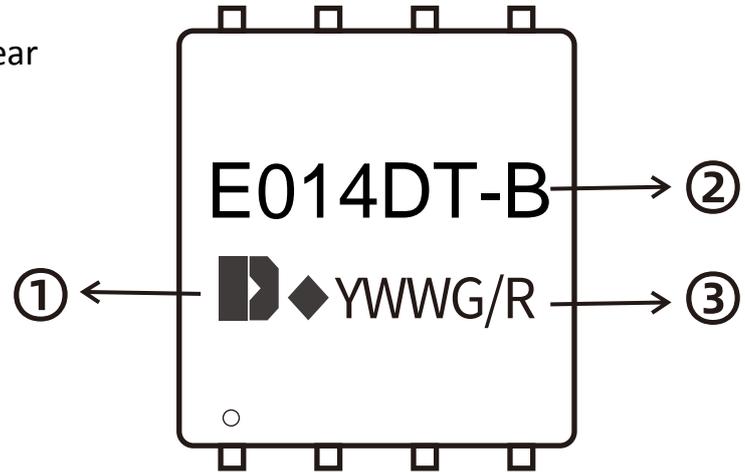
Marking Information:

- ①. Doingter LOGO
- ②. Part NO.
- ③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-05-12	Release of final version

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